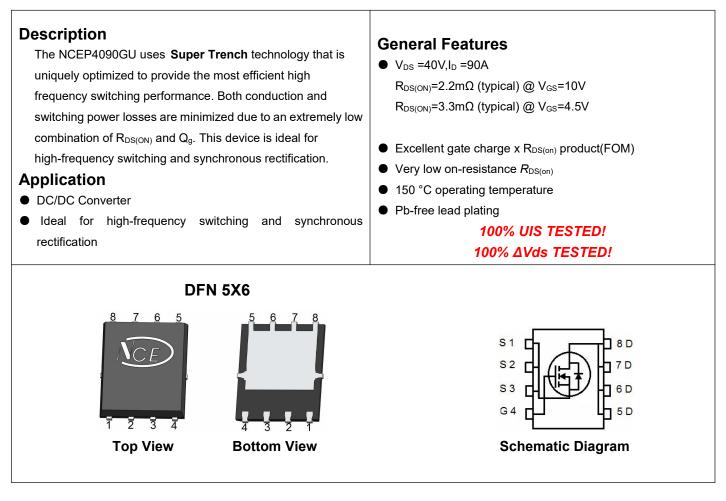




NCE N-Channel Super Trench Power MOSFET



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
P4090GU	NCEP4090GU	DFN5x6-8L	-	-	-

Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Par	Parameter		Limit	Unit
Drain-Source Voltage		VDS	40	V
Gate-Source Voltage		Vgs	±20	V
Drain Current-Continuous	(T _C =25℃)	1	90	A
Drain Current-Continuous	(T _C =100℃)	- I _D	63.6	
	(T _C =25℃)	D	85	\A/
Maximum Power Dissipation	(Tc=100℃)		34	W
Pulsed Drain Current		I _{DM}	360	А
Derating factor			0.68	W/℃
Single pulse avalanche energy	Note 1)	E _{AS}	500	mJ
Operating Junction and Storage	Temperature Range	T _J ,T _{STG}	-55 To 150	°C



Thermal Characteristic

Thermal Resistance, Junction-to-Case	R _{ejc}	1.47	°C/W
--------------------------------------	------------------	------	------

Electrical Characteristics (Tc=25 $^{\circ}$ C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Мах	Unit
Off Characteristics	· · ·					
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	40		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	±100	nA
On Characteristics	· · ·					
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	1.0	1.5	2.2	V
		V _{GS} =10V, I _D =20A	-	2.2	2.75	mΩ
Drain-Source On-State Resistance	Rds(on)	V_{GS} =4.5V, I _D =20A	-	3.3	4.0	mΩ
Forward Transconductance	g fs	V _{DS} =5V,I _D =20A		60	-	S
Dynamic Characteristics						
Input Capacitance	C _{lss}	V _{DS} =20V,V _{GS} =0V,	-	2300	-	PF
Output Capacitance	Coss		-	740	-	PF
Reverse Transfer Capacitance	Crss	F=1.0MHz	-	38	-	PF
Switching Characteristics (Note 2)	· ·					
Turn-on Delay Time	t _{d(on)}		-	7.5	-	nS
Turn-on Rise Time	tr	V _{DD} =20V,I _D =20A	-	4.0	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{G} =1.6 Ω	-	37	-	nS
Turn-Off Fall Time	t _f		-	7.5	-	nS
Total Gate Charge	Qg	N/ 001/1 004	-	40	-	nC
Gate-Source Charge	Qgs	$V_{DS}=20V, I_{D}=20A,$	-	5.8		nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	7.2		nC
Drain-Source Diode Characteristics				I	I	
Diode Forward Voltage	Vsd	V _{GS} =0V,I _S =20A	-		1.2	V
Diode Forward Current	ls		-	-	90	A
Reverse Recovery Time	t _{rr}	TJ = 25°C, I⊧ = Is	-	14	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs	-	21	-	nC

Notes:

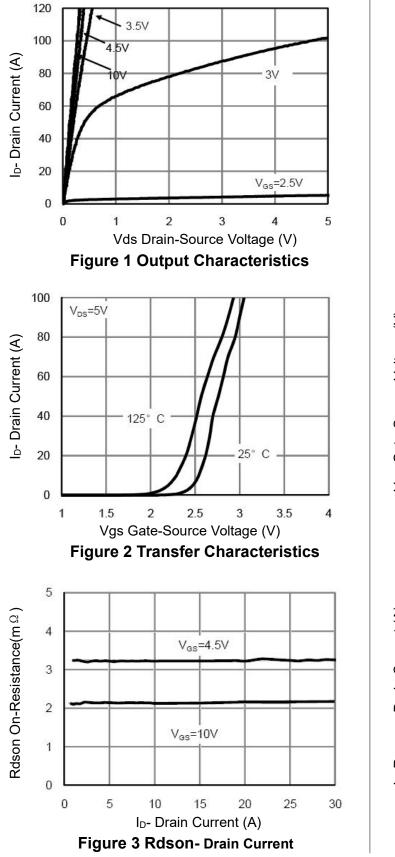
1. EAS condition : Tj=25 $^{\circ}$ C,V_{DD}=20V,V_G=10V,L=0.5mH,Rg=25 Ω

2. Guaranteed by design, not subject to production

3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsin k, assuming a maximum junction temperature of TJ(MAX)=150° C. The SOA curve provides a single pulse rating.



Typical Electrical and Thermal Characteristics



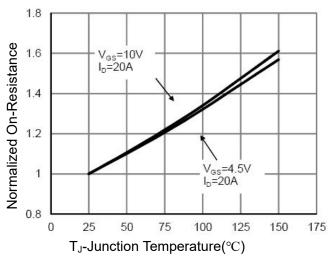
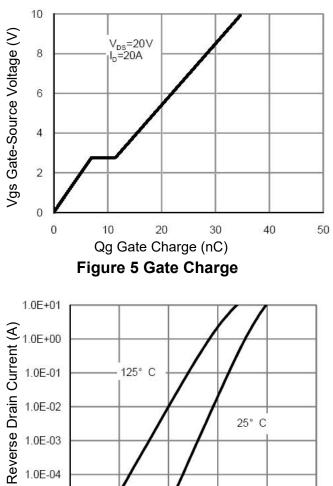
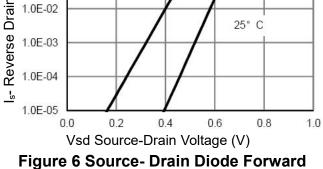


Figure 4 Rdson-Junction Temperature

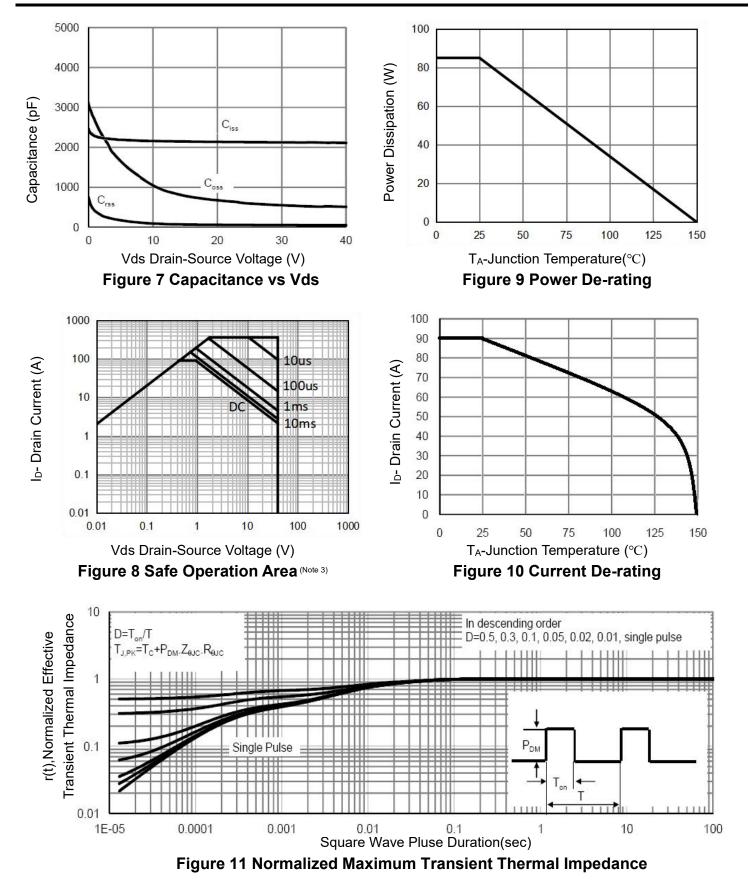






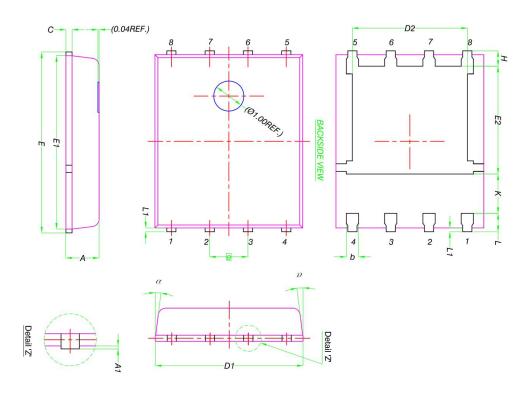
http://www.ncepower.com

NCEP4090GU





DFN5X6-8L(G) Package Information



					Land	Patterr
-	٨	<i>ILLIMET</i>	ERS	(0	Only for 7	Refere
DIM.	MIN.	NOM.	MAX.	8	7	6
А	0.90	1.00	1.10		\mathbf{X}	\boxtimes
A1	0	÷	0.05			
b	0.33	0.41	0.51			
С	0.20	0.25	0.30		\sim	$\sim \sim$
D1	4.80	4.90	5.00	4.52	\sim	\sim
D2	3.61	3.81	3.96	4	3.81	
Ε	5.90	6.00	6.10			$\sim \sim \sim$
E1	5.70	5.75	5.80		3.	91
E2	3.38	3.58	3.78			
е		1.27 BSC				\sim
Н	0.41	0.51	0.61	1	-1.	27
К	1.10	-	-	KK		KX
L	0.51	0.61	0.71	1.27	N/A	XX.
L1	0.06	0.13	0.20	7		0.61
α	0°	-	12°			42
		÷		1	2 4.	42

4.32-6.61

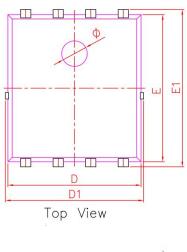
Note:

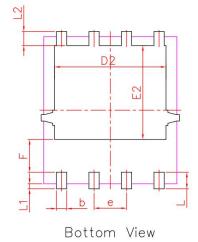
All Dimension Are In mm.
Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs.

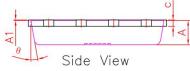
- Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side. 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic
- Body Exclusive Of Mold Flash, Tie Bar, Tie Bar Burrs, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body. 4. The Package Top May Be Smaller Than The Package Bottom.



DFN5X6-8L(E) Package Information







DIM.	MIN.	NOM.	MAX.		
A	0.90	0.95	1.00		
A1	0.00	0.02	0.05		
b	0.35	0.40	0.50		
С	0.20	0.25	0.30		
D	5.10	5.20	5.30		
D1	5.10	5.40	5.50		
D2	4.25	4.35	4.45		
е	1.27 BSC				
E	5.70	5.75	5.80		
E1	6.00	6.15	6.30		
E2	3.57	3.67	3.77		
F	1.18	1.28	1.38		
L	0.55	0.65	0.75		
L1	0.15	0.20	0.25		
L2	0.45	0.55	0.65		
Ø	0.90	1.00	1.10		
Θ	8*	10°	12*		



Attention:

- Any and all NCE power products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your NCE power representative nearest you before using any NCE power products described or contained herein in such applications.
- NCE power assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all NCE power products described or contained herein.
- Specifications of any and all NCE power products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- NCE power Semiconductor CO.,LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all NCE power products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of NCE power Semiconductor CO.,LTD.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. NCE power believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the NCE power product that you intend to use.
- This catalog provides information as of Sep.2010. Specifications and information herein are subject to change without notice.